

**AMENDMENTS TO THE CLAIMS**

Applicant submits below a complete listing of the current claims, including marked-up claims with insertions indicated by underlining and deletions indicated by strikeouts and/or double bracketing. This listing of claims will replace all prior versions, and listings, of claims in the application:

1. (Withdrawn) An apparatus comprising:  
a source of an incident electromagnetic wave;  
a first plate of material transparent to the electromagnetic wave; and  
a layer of phase shift material having defined therethrough a polygonal window with  
at least six sides.
2. (Withdrawn) The apparatus according to claim 1, wherein said layer is adapted to  
define features of a semiconductor device.
3. (Withdrawn) The apparatus according to claim 1, wherein said polygonal window is  
octagonal.
4. (Withdrawn) The apparatus according to claim 1, wherein said polygonal window  
has such a number of sides as to form an approximately circular shape.
5. (Withdrawn) The apparatus according to claim 1, wherein said layer of phase shift  
material causes a 180° phase shift of the incident electromagnetic wave.
6. (Withdrawn) The apparatus according to claim 1, wherein said layer of phase shift  
material at least partially absorbs the incident electromagnetic wave at the wavelength used.

7. (Currently amended) A method of defining contacts on an integrated circuit device using an ~~electromagnetic~~ incident wave including:

providing an integrated circuit device substrate, a first plate of material transparent to the ~~electromagnetic~~ incident wave placed over the substrate, and a layer of phase shift material having defined therethrough a ~~regular polygonal~~ regular polygon-shaped etch window with at least six sides; and

directing the ~~electromagnetic~~ incident wave at the substrate through the layer of phase shift material and first plate.

8. (Currently amended) The method according to claim 7, wherein the layer causes a 180° phase shift of the ~~electromagnetic~~ incident wave.

9. (Currently amended) The method according to claim 7, wherein the layer partially absorbs the ~~electromagnetic~~ incident wave.

10. (Withdrawn) An integrated circuit contact formed by directing an electromagnetic wave at a substrate through a first plate of material transparent to the electromagnetic wave placed over the substrate, and a layer of phase shift material placed over the first plate having defined therethrough a polygonal etch window with at least six sides.

11. (Withdrawn) The integrated circuit contact according to claim 10, formed by an octagonal window.

12. (Withdrawn) The integrated circuit contact according to claim 10, formed by a polygonal etch window having such a number of sides as to form an approximately circular shape.

13. (Withdrawn) The integrated circuit contact according to claim 12, wherein the layer of phase shift material causes a 180° phase shift of the photoelectric wave.

14. (Withdrawn) The integrated circuit contact according to claim 10, wherein the layer made of transparent material partially absorbs the photoelectric wave.